

# Low-Power, RRIO, 1MHz Operational Amplifier for Cost-Sensitive Systems

#### **General Description**

ET85002 is a dual low-voltage (1.8 V to 5.5 V) operational amplifiers with rail-to-rail input and output swing capabilities. ET85002 provides a cost-effective solution for space-constrained applications such as smoke detectors, wearable electronics, and small appliances where low-voltage operation and high capacitive-load drive are required. The capacitive-load drive is 500 pF and the resistive open-loop output impedance makes stabilization easier with much higher capacitive-loads. ET85002 features the unity-gain stability and integrated RFI and EMI rejection filter and no-phase reversal in overdrive conditions.

ET85002 is specified for the extended industrial / automotive temperature range (-40°C to +125°C). ET85002 is available in SOP8 / MSOP8/DFN8 packages.

#### **Features**

- Dual CMOS amplifier for low-cost applications
- Rail-to-rail input and output
- Low input offset voltage: ±0.4 mV
- Unity-gain bandwidth: 1 MHz
- Low broadband noise: 27 nV/√Hz
- Low input bias current: 5 pA
- Low quiescent current: 60 μA/Ch
- Unity-gain stable
- Internal RFI and EMI filter
- Operational at supply voltages as low as 1.8 V
- Easier to stabilize with higher capacitive load
- Extended temperature range: -40°C to 125°C

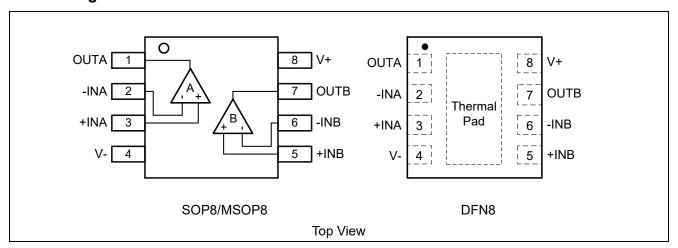
#### **Applications**

- Temperature sensors
- Sensor signal conditioning
- Power modules
- Active filters
- Low-side current sensing

#### **Device information**

Part No.	Package	Tape / Reel
ET85002M	SOP8	Tape and Reel 4K
ET85002U	MSOP8	Tape and Reel 4K
ET85002Y	DFN8(2×2)	Tape and Reel 3K

#### **Pin Configuration**



#### **Pin Function**

Pin Number		
ET85002M/U/Y	Symbol	Descriptions
1,7	OUT	Output
4	V-	Negative supply
3,5	+IN	Non-inverting input
2,6	-IN	Inverting input
8	V+	Positive supply

#### **Functional Description**

#### **Operating Voltage**

ET85002 is for operation from 1.8 V to 5.5 V. In addition, many specifications such as input offset voltage, quiescent current, offset current, and short circuit current apply from -40°C to 125°C.

#### Rail-to-Rail Input

The input common-mode voltage range extends 100 mV beyond the supply rails for the full supply voltage range of 1.8 V to 5.5 V. This performance is achieved with a complementary input stage.

#### Rail-to-Rail Output

Designed as a low-power, low-voltage operational amplifier, the ET85002 delivers a robust output drive capability. A class AB output stage with common-source transistors achieves full rail-to-rail output swing

capability. For resistive loads of 10  $k\Omega$ , the output swings to within 20 mV of either supply rail, regardless of the applied power-supply voltage. Different load conditions change the ability of the amplifier to swing close to the rails.

#### **Device Functional Modes**

ET85002 has a single functional mode. The devices are powered on as long as the power-supply voltage is between 1.8 V ( $\pm 0.9$  V) and 5.5 V ( $\pm 2.75$  V).

#### **Absolute Maximum Ratings**

Stresses beyond those listed under Absolute Maximum Ratings may cause permanent damage to the device. These are only stress ratings, and functional operation of the device at these or any other conditions beyond those indicated under recommended operating conditions are not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

Parameter	Rating	Unit
Supply Voltage <sup>(1)</sup> (V+) - (V-)	6.0	V
Input Voltage	(V-)-0.3V to (V+)+0.3	V
Differential Input Voltage	(V+) - (V-)+0.2	V
ESD (Human Body Model)	±2000	V
Storage Temperature Range	-65 to +150	°C
Max Junction Temperature	+150	°C
Lead Temperature Range (Soldering, 60 sec)	300	°C

**Note1**: All voltage values, except differential voltage are with respect to network terminal.

#### **Recommended Operating Conditions**

Parameter	Min	Max	Unit
Supply Voltage (Vs)	1.8	5.5	V
Operating Temperature (T <sub>A</sub> )	-40	125	°C

#### **Thermal Characteristics**

Symbol	Package	Ratings	Value	Unit
	SOP8	160	°C/W	
RөJA	MSOP8	Thermal Characteristics,  Thermal Resistance, Junction-to-Air	200	°C/W
	DFN8(2×2)		160	°C/W

### **Electrical Characteristics**

 $V_S$  = (V+) - (V-) = 1.8 V to 5.5 V (± 0.9 V to ± 2.75 V),  $T_A$  = 25°C,  $R_L$  = 10 k $\Omega$  connected to  $V_S/2$ , and  $V_{CM}$  =  $V_{OUT}$  =  $V_S/2$  (unless otherwise noted)

Symbol	Parameter	Conditions	Min	Тур	Max	Unit	
OFFSET VOLTAGE							
.,		Vs = 5 V		±0.4	±1.6		
Vos	Input offset voltage	V <sub>S</sub> = 5 V, T <sub>A</sub> = -40°C to 125°C			±2	mV	
dVos/dT	Vos vs temperature	T <sub>A</sub> = -40°C to 125°C		±0.6		μV/°C	
PSRR	Power-supply rejection ratio	V <sub>S</sub> = 1.8 to 5.5 V, V <sub>CM</sub> = (V-)	80	105		dB	
INPUT \	OLTAGE RANGE						
V <sub>СМ</sub>	Common-mode voltage range	No phase reversal, rail-to-rail input	(V-)-0.1		(V+)+0.1	٧	
		V <sub>S</sub> = 1.8 V,					
		$(V-) - 0.1 V < V_{CM} < (V+) - 1.4 V,$ $T_A = -40^{\circ}C \text{ to } 125^{\circ}C$		86			
		V <sub>S</sub> = 5.5 V,				_	
		VS = 3.5  V, $(V-) - 0.1 \text{ V} < V_{CM} < (V+) - 1.4 \text{ V},$		95			
	Common-mode rejection ratio	$T_A = -40^{\circ}\text{C to } 125^{\circ}\text{C}$		00			
CMRR		V <sub>S</sub> = 5.5 V,				dB	
		(V-) -0.1 V < V <sub>CM</sub> < (V+) + 0.1 V,		77			
		T <sub>A</sub> = -40°C to 125°C					
		V <sub>S</sub> = 1.8 V,					
		$(V-) - 0.1 V < V_{CM} < (V+) + 0.1 V,$		68			
		T <sub>A</sub> = -40°C to 125°C					
INPUT I	BIAS CURRENT						
lΒ	Input bias current	V <sub>S</sub> = 5 V		±5		pА	
los	Input offset current			±2		pА	
NOISE							
En	Input voltage noise (peak to peak)	$f = 0.1 \text{ Hz to } 10 \text{ Hz}, \text{ V}_{\text{S}} = 5 \text{ V}$		4.7		μV <sub>PP</sub>	
	Input voltage	f = 1 kHz, Vs = 5 V		30			
e <sub>n</sub>	noise density	f = 10 kHz, Vs = 5 V		27		nV/√Hz	
	Input current	-				60//	
İn	noise density (2)	$f = 1 \text{ kHz}, V_S = 5 \text{ V}$	23			fA/√Hz	
INPUT CAPACITANCE (2)							
C <sub>ID</sub>	Differential	1.5			pF		
C <sub>IC</sub>	Common-mode			5		pF	

## **Electrical Characteristics (Continued)**

Symbol	Parameter	Conditions	Min	Тур	Max	Unit	
OPEN-LOOP GAIN							
		$V_S = 5.5 \text{ V}, R_L = 10 \text{ k}\Omega$	104	117			
		$(V-) + 0.05 V < V_0 < (V+) - 0.05 V$	104	117			
		$V_S = 1.8 \text{ V}, R_L = 10 \text{ k}\Omega$		100			
Avo	Open-loop	$(V-) + 0.04 V < V_O < (V+) - 0.04 V$		100		dB	
Avo	voltage gain	$V_S = 1.8 \text{ V}, R_L = 2 \text{ k}\Omega$		115		uБ	
		$(V-) + 0.1 V < V_0 < (V+) - 0.1 V$		110			
		$V_S = 5.5 \text{ V}, R_L = 2 \text{ k}\Omega$		130			
		$(V-) + 0.15 V < V_0 < (V+) - 0.15 V$	130				
FREQU	ENCY RESPONSE						
GBW	Gain-bandwidth product	V <sub>S</sub> = 5 V		1		MHz	
φm	Phase margin	V <sub>S</sub> = 5 V, G = 1		78		0	
SR	Slew rate	Vs = 5 V		2		V/µs	
	Settling time (2)	To 0.1%, Vs = 5 V, 2V step,	2.5				
ts		G = +1, C <sub>L</sub> = 100 pF		2.5		μs	
ıs		To 0.01%, V <sub>S</sub> = 5 V, 2V step,		3			
		G = +1, C <sub>L</sub> = 100 pF		<u> </u>			
tor	Overload	Vs = 5 V, V <sub>IN</sub> × gain > Vs		0.85		μs	
tort	recovery time	vo ov, viiv gain vo		0.00		μο	
THD+N	Total harmonic	$V_S = 5.5 \text{ V}, V_{CM} = 2.5 \text{ V},$	0.0	0.004	4	%	
1110 111	distortion + noise	$V_0 = 1 V_{RMS}, G = +1, f = 1 kHz,$		0.001		70	
OUTPU	Т		1 1		ı		
Vo	Voltage output swing	$V_{S} = 5.5 \text{ V}, R_{L} = 10 \text{ k}\Omega$		10	20	mV	
• •	from supply rails	$V_{S} = 5.5 \text{ V}, R_{L} = 2 \text{ k}\Omega$		35	55		
I <sub>SC</sub>	Short-circuit current	V <sub>S</sub> = 5.5 V		±40		mA	
Zo	Open-loop output impedance (2)	Vs = 5 V, f = 1 MHz		1200		Ω	
POWER SUPPLY							
\ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \	Specified		4.0 (+0.0)		F F ( : 0.75)	\/	
Vs	voltage range		1.8 (±0.9)		5.5 (±2.75)	V	
	Quinagert surrent	$I_0 = 0 \text{ mA}, V_S = 5.5 \text{ V}$	60	82			
ΙQ	Quiescent current	I <sub>O</sub> = 0 mA, V <sub>S</sub> = 5.5 V,			0.5	μA	
	per amplifier	T <sub>A</sub> = -40°C to 125°C			85		

Note2: Guaranteed by design.

#### **Application Notes**

#### **Layout Guidelines**

For best operational performance of the device, use good PCB layout practices, including:

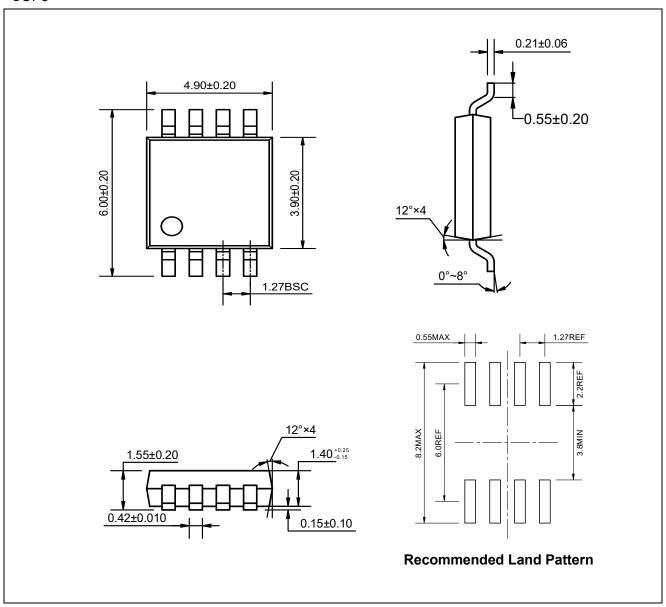
Place the external components as close to the device as possible. This configuration prevents parasitic errors (such as the Seebeck effect) from occurring.

To reduce parasitic coupling, run the input traces as far away from the supply lines and digital signal as possible.Low-ESR, 0.1µF ceramic bypass capacitors must be connected between each supply pin and ground, placed as close to the device as possible. A single bypass capacitor from V+ to ground is applicable to single supply applications.

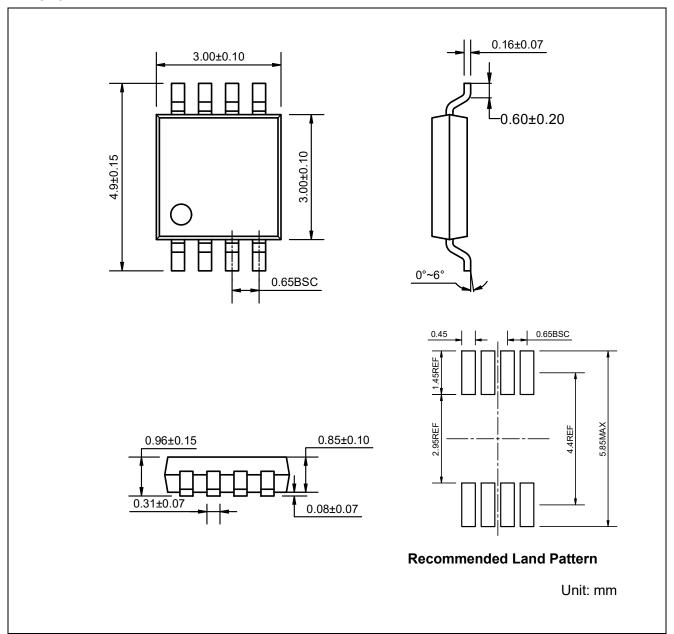
Consider a driven, low-impedance guard ring around the critical traces. A guard ring can significantly reduce leakage currents from nearby traces that are at different potentials.

## **Package Dimension**

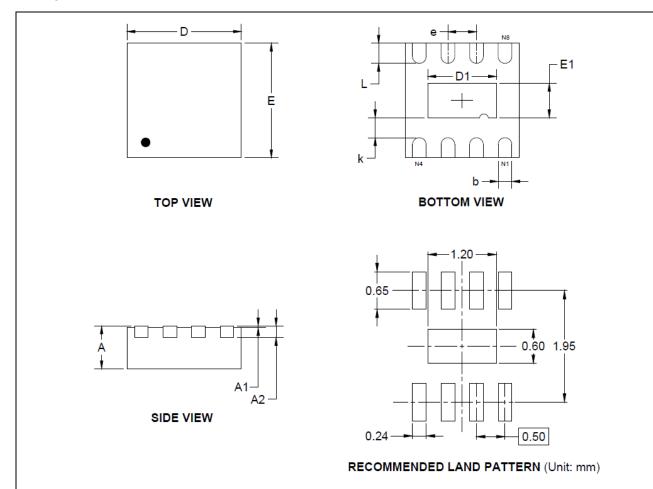
SOP8



#### MSOP8



#### DFN8-2×2



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	MIN	MAX	MIN	MAX
Α	0.700	0.800	0.028	0.031
A1	0.000	0.050	0.000	0.002
A2	0.203	REF	0.008 REF	
D	1.900	2.100	0.075	0.083
D1	1.100	1.300	0.043	0.051
E	1.900	2.100	0.075	0.083
E1	0.500	0.700	0.020	0.028
k	0.200	0.200 MIN 0.008 N		MIN
b	0.180	0.300	0.007	0.012
е	0.500 TYP		0.020	TYP
L	0.250	0.450	0.010	0.018

## **Revision History and Checking Table**

Version	Date	Revision Item	Modifier	Function & Spec Checking	Package & Tape Checking
0.0	2022-9-21	Preliminary Version	Shibo	Wanggp	Liujy
1.0	2023-9-27	Original Version	Huyt	Chenh	Liujy
1.1	2024-11-27	IQ max changed 82uA	Shibo	Wanggp	Liujy